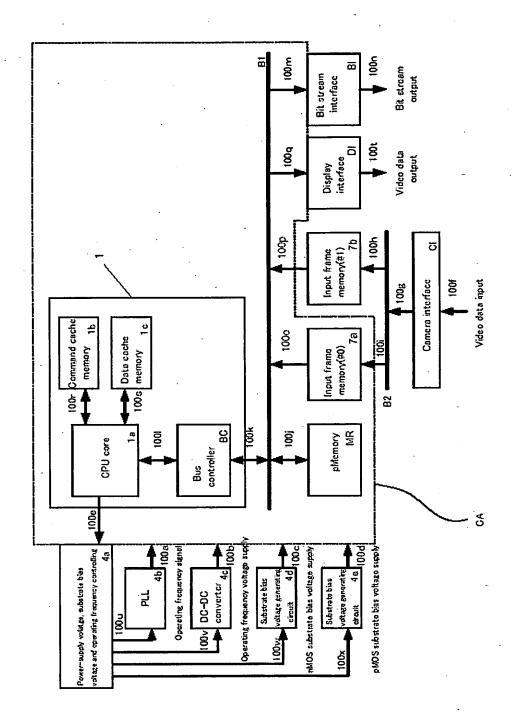
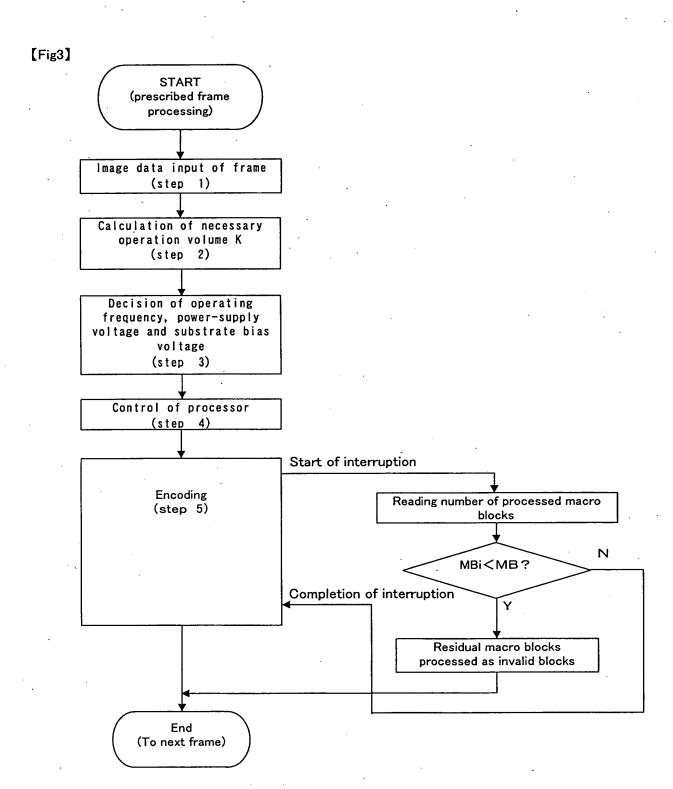


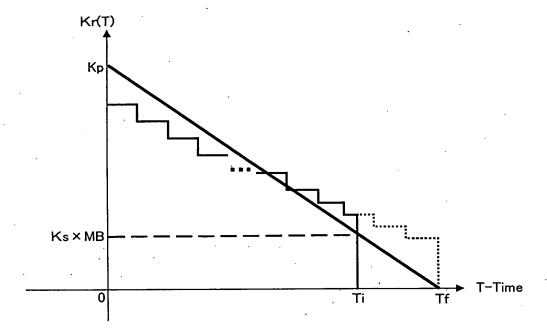
Means of controlling power-supply voltage, substrate bias voltage and operating frequency 4

[Fig2]





[Fig4]

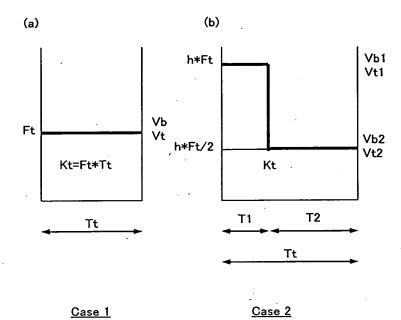


[Fig5]

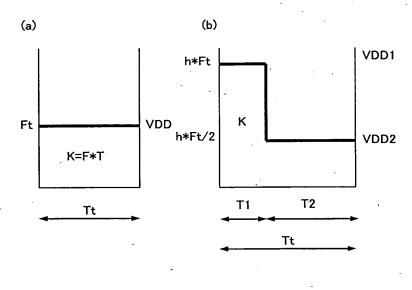
Operating frequency (cycles/second)	Power-supply voltage (VDD)	Substrate bias voltage of n-channel MOS transistor (Vbn)	
f (1)	VDD (1)	Vbn (1)	Vbp (1)
f (2) (>f (1))	VDD (2)	Vbn (2)	Vbp (2)
f (3) (>f (2))	VDD (3)	Vbn (3)	Vbp (3)
•	•	•	٠.
f (n) (>f (n-1))	VDD (n)	Vbn (n)	Vbp (n)
	•	•	•
f (r) (>f (r-1))	VDD (r)	Vbn (r)	Vbp (r)



[Fig7]

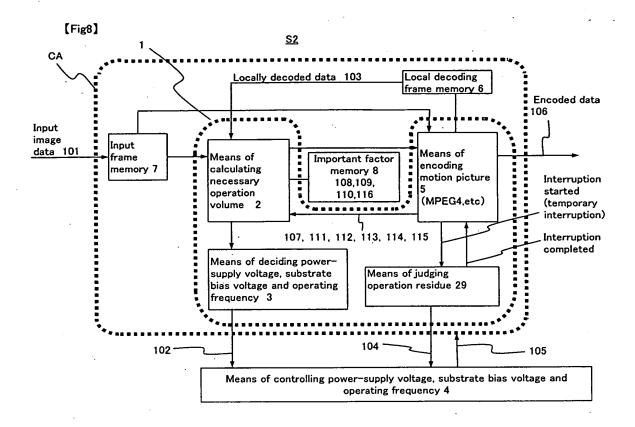


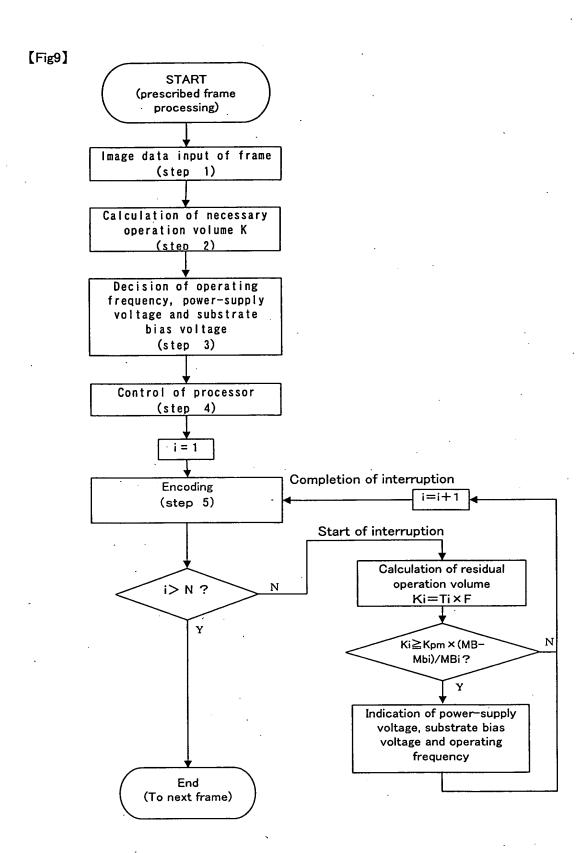
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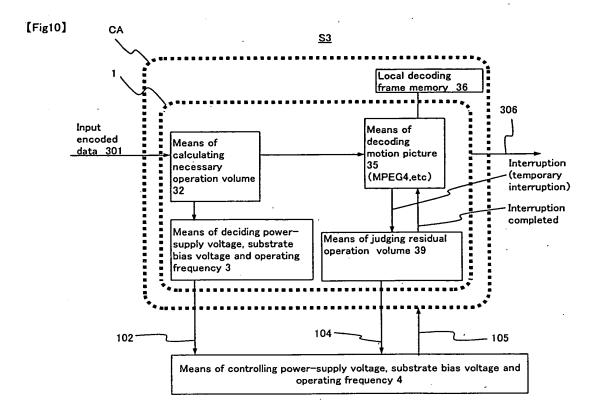


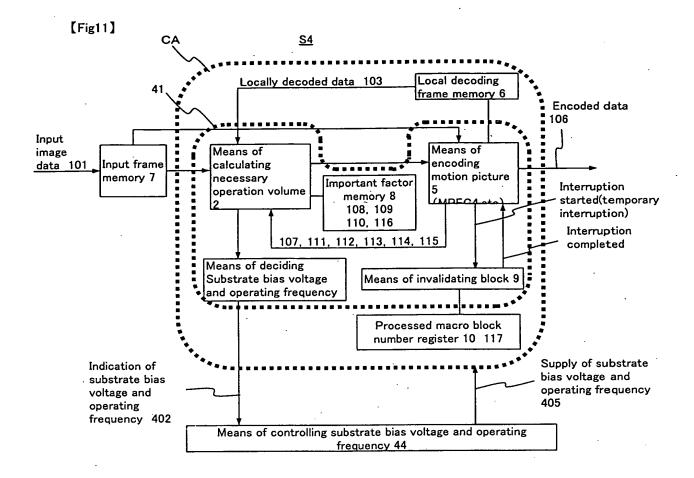
Case 1

Case 2







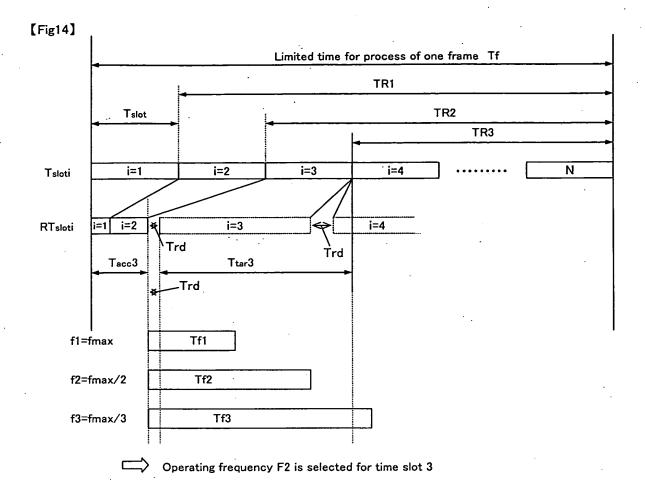


[Fig12]

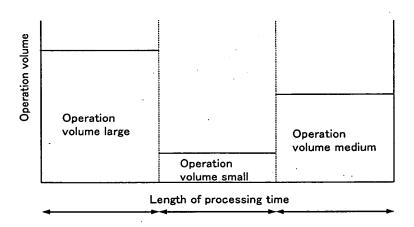
Operating frequency (cycles/second)	Substrate bias voltage of n-channel MOS transistor (Vbn)	Substrate bias voltage of p-channel MOS transistor (Vbp)
f (1)	Vbn (1)	Vbp (1)
f (2) (>f (1))	Vbn (2)	Vbp (2)
f (3) (>f (2))	Vbn (3)	Vbp (3)
•	•	. •
f (n) (>f (n-1))	Vbn (n)	Vbp (n)
	•	•
f (r) (>f (r-1))	V.bn (r)	Vbp (r)

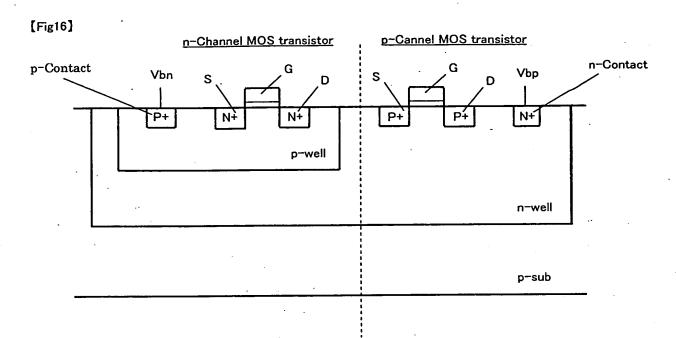
[Fig13]

Operating frequency (cycles / second)		Substrate bias voltage of n-channel MOS transistor (Vbn)	
f(1)=50	VDD(1)=0.5	Vbn (1) = -1.0	Vbp (1) = 1.5
f(2) = 100	VDD(2) = 0.6	Vbn (2) = -0.4	Vbp (2) = 1.0
f(3)=150	VDD(3) = 0.8	Vbn (3) = 0	Vbp (3) = 0.8
f (4)=200	VDD(4)=0.9	Vbn $(4) = 0.2$	Vbp (4) = 0.7
f (5)=250	VDD(5)=1.0	Vbn(5) = 0.5	Vbp (5) = 0.5

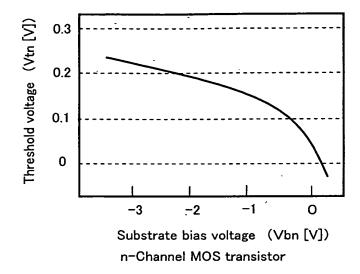


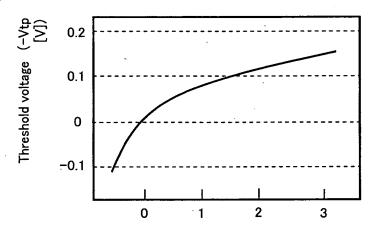
[Fig15]





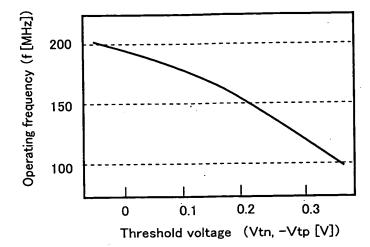
[Fig17]





Substrate bias voltage (Vbp [V])—Power-supply voltage (VDD [V]) p-Channel MOS transistor

[Fig18]



[Fig19]

